



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

•			
Para	meter	Value	Units
Collector-Base Voltage	: BD135	45	V
	: BD137	60	V
	: BD139	80	V
Collector-Emitter Voltage	: BD135	45	V
	: BD137	60	V
	: BD139	80	V
Emitter-Base Voltage		5	V
Collector Current (DC)		1.5	Α
Collector Current (Pulse)		3.0	Α
Base Current		0.5	Α
Collector Dissipation (T _C =25°C	C)	12.5	W
Collector Dissipation (T _a =25°C	:)	1.25	W
Junction Temperature		150	°C
Storage Temperature		- 55 ~ 150	°C
	Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Collector Current (DC) Collector Current (Pulse) Base Current Collector Dissipation (T _C =25°C Collector Dissipation (T _a =25°C Junction Temperature	: BD137 : BD139 Collector-Emitter Voltage : BD135 : BD137 : BD137 : BD139 Emitter-Base Voltage Collector Current (DC) Collector Current (Pulse) Base Current Collector Dissipation (T _C =25°C) Collector Dissipation (T _a =25°C) Junction Temperature	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

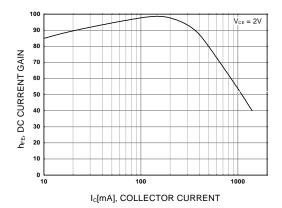
Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage					
	: BD135	$I_{C} = 30 \text{mA}, I_{B} = 0$	45			V
	: BD137	0 0	60			V
	: BD139		80			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 30V, I_{E} = 0$			0.1	μΑ
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$				

h_{FE} Classification

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Typical Characteristics



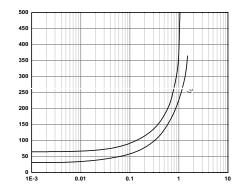


Figure 1. DC current Gain

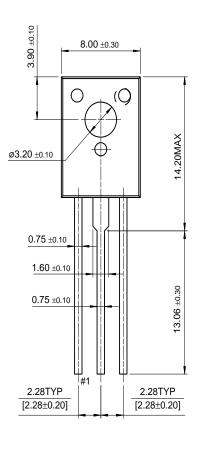
Figure 2. Collector-Emitter Saturation Voltage

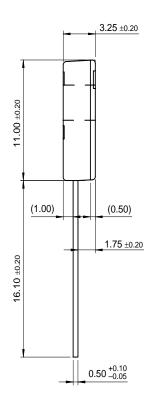
Figure 3. Base-Emitter Voltage

Figure 4. Safe Operating Area

Figure 5. Power Derating

TO-126





Dimensions in Millimeters

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